

European IBIS Summit

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IBIS + Mpilog: Current and Future Developments on I/O-Buffer Modeling

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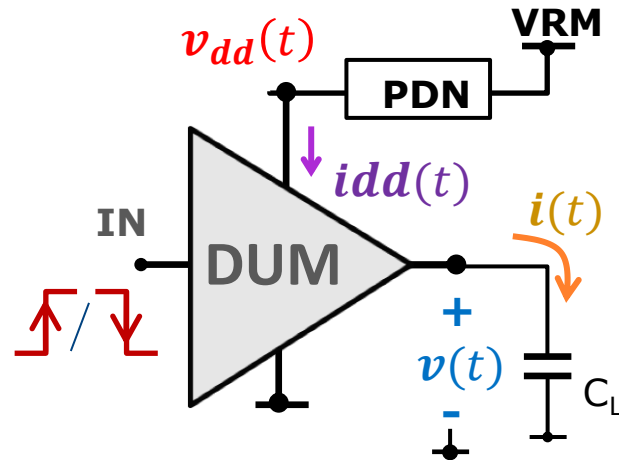
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Agenda

1. Macromodels for SI&PI: Requirements
2. IBIS, Two-piece Macromodels & Power-Awareness (?)
3. Enhanced Macromodels (Mpilog-class)
4. Possible Enhancements to IBIS
5. Conclusions

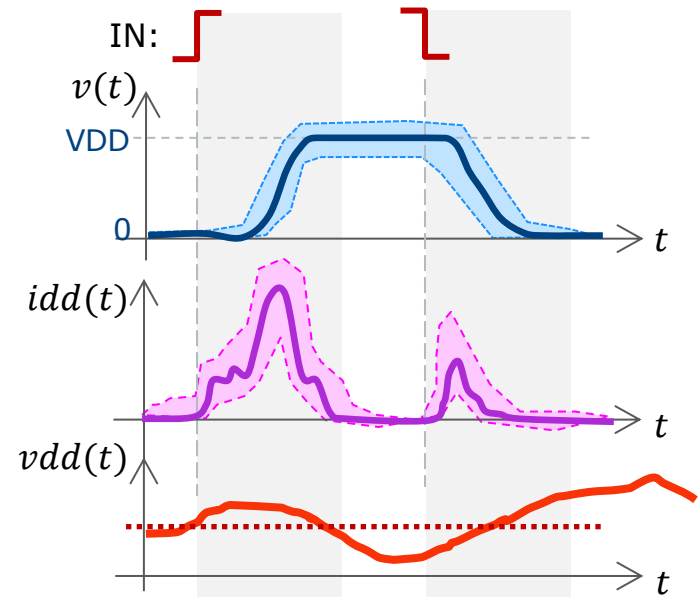
Requirements for I/O Macromodels



Accuracy at Output Port ($v(t)$, $i(t)$)

- + Supply-Current Profile ($i_{dd}(t)$)
- + Supply-Voltage Noise ($v_{dd}(t)$)
- + Supply-Noise Effects ($f(\Delta v_{dd})$)

= I/O-buffer model for SI&PI

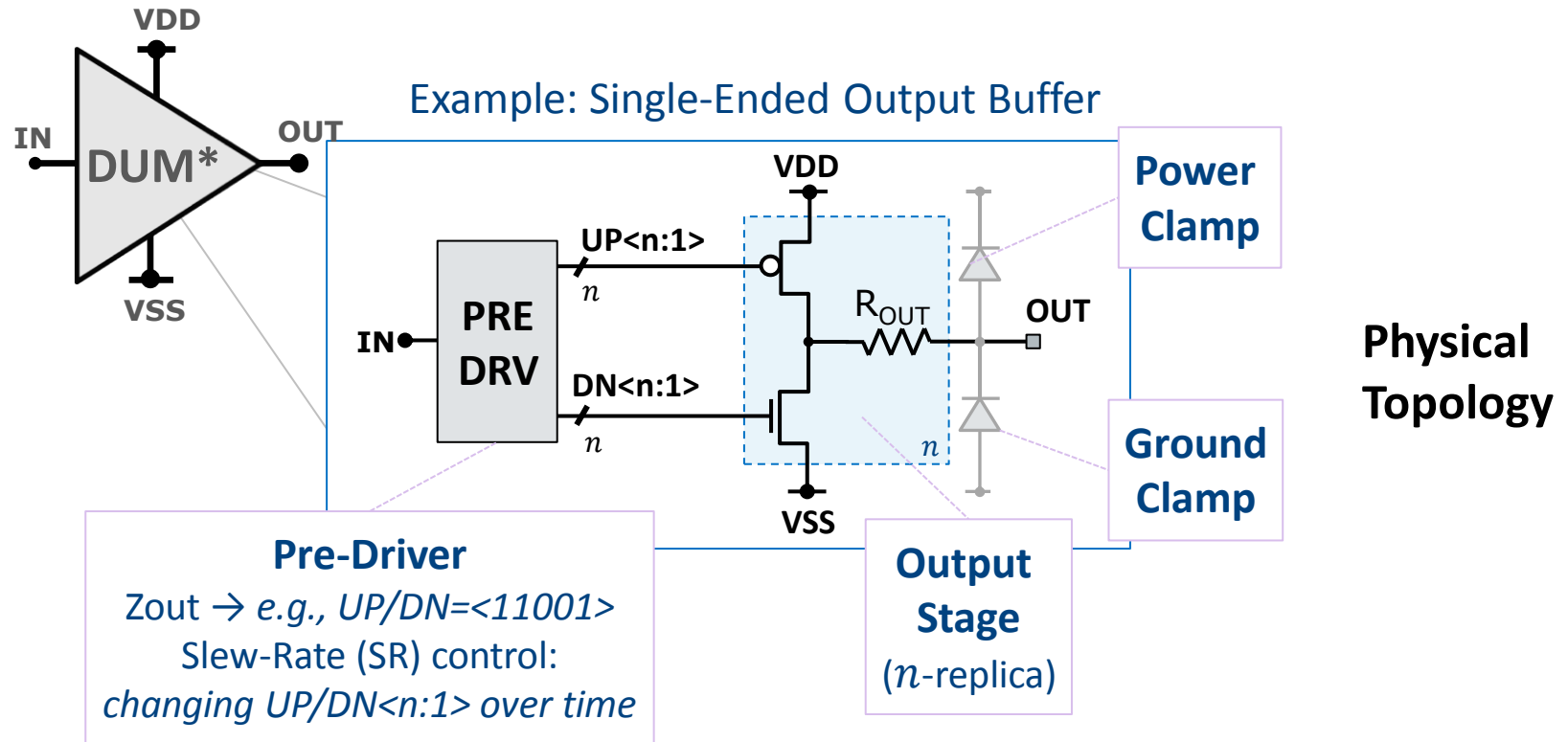


Targets:

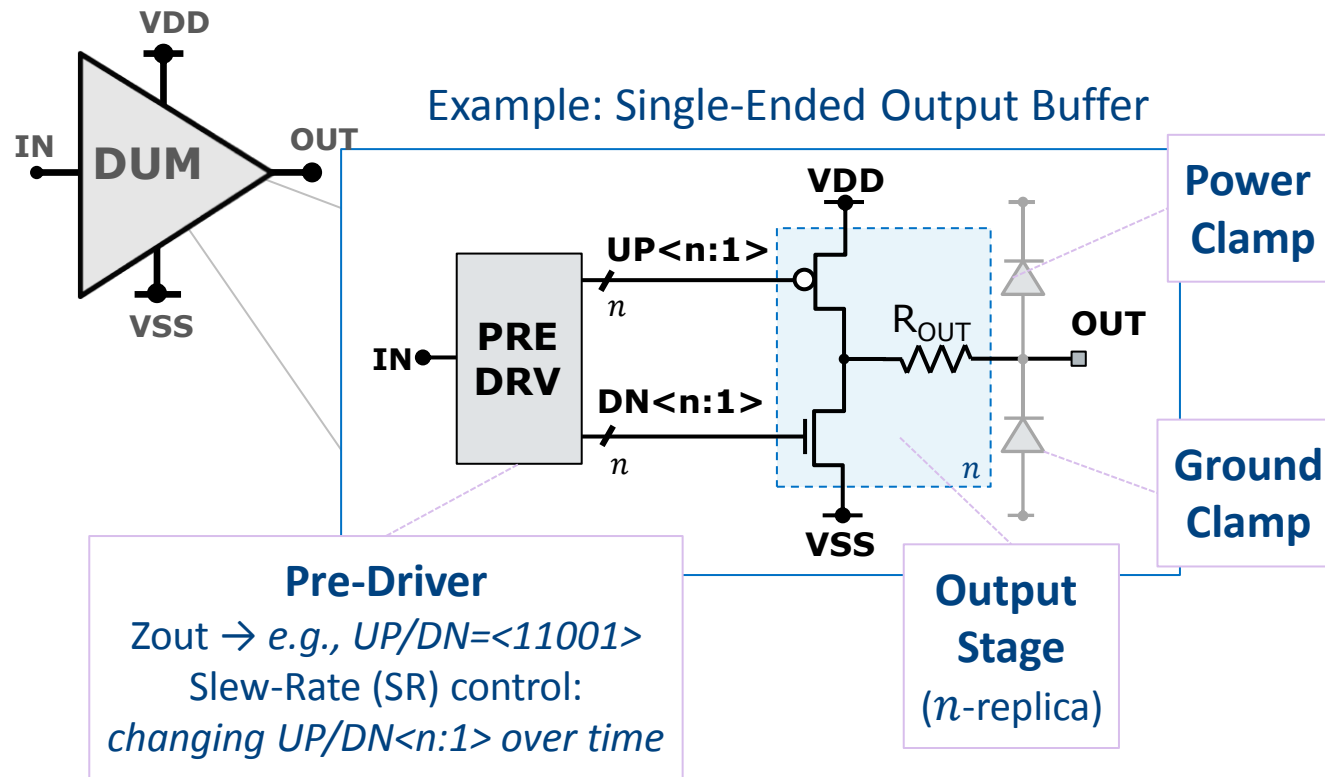
$$\begin{cases} v(t), i(t) \\ v_{dd}(t), i_{dd}(t) \\ \Delta t, \Delta v_{out}, \Delta i_{dd} = f(\Delta v_{dd}) \end{cases}$$

Two-piece Model Structure

*DUM = Device Under Modeling



Two-piece Model Structure



Physical
Topology

$$i(t) = w_H(t) \cdot I_{PU}(v) + w_L(t) \cdot I_{PD}(v) - C_{COMP} \frac{\partial v}{\partial t}$$

Pull-Up
Pull-Down
"Dynamic"

Up/Down Events

Two-piece
Model

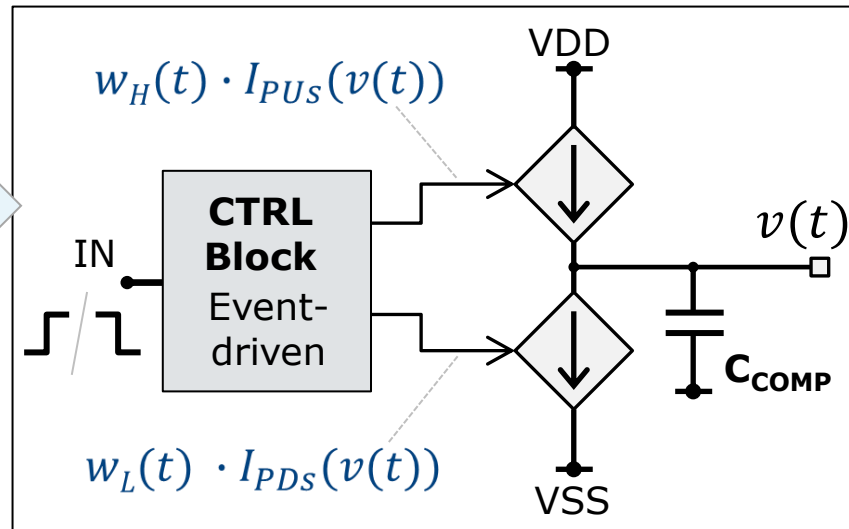
IBIS v3.2 & Two-piece Model Structure

$$i(t) = w_H(t) \cdot I_{PU}(v) + w_L(t) \cdot I_{PD}(v) - C_{COMP} \frac{\partial v}{\partial t}$$

my_ibis.ibs

```
[Model]
[Pull-Up]
  v1 i1
  v2 i2
  ...
[Pull-Down]
[C_comp]
[Rising Waveform]
  t1 v1
  t2 v2
  ...
[Falling Waveform]
```

IBIS v3.2 Equivalent Electrical Circuit



$$i(t), v(t) @ VDD_{NOM} = \text{☺}$$



Limitation:

$$\begin{cases} i_{dd}(t) = ? / \text{☹} \\ v_{dd}(t) \neq VDD_{NOM} \Rightarrow ??? / \text{☹} \end{cases}$$

Power-awareness in IBIS (v5.0)

$$i(t) = w_H(t) \cdot I_{PU}(v) + w_L(t) \cdot I_{PD}(v) - C_{COMP} \frac{\partial v}{\partial t} \quad \text{IBIS v3.2}$$

**“Power-Aware”
Two-piece Model**

$$i(t) = w_H(t) \cdot K_{SSOPU}(\Delta v_{dd}) \cdot I_{PU}(v) + w_L(t) \cdot K_{SSOPD}(\Delta v_{ss}) \cdot I_{PD}(v) - C_{COMP} \partial v / \partial t$$

$$i_{dd}(t) = w_H(t) \cdot K_{SSOPU}(\Delta v_{dd}) \cdot I_{PU}(v) + \partial i(t)$$

IBIS v5.0

KSSO_PU/PD

introduce approximations of supply/ground noise on output static characteristics

Supply-current is explicitly modeled, and corresponds to **pull-up** and **“crow-bar”/other current** contributions

Power-awareness in IBIS (v5.0)

“Power-Aware” Two-piece Model = IBIS v5.0

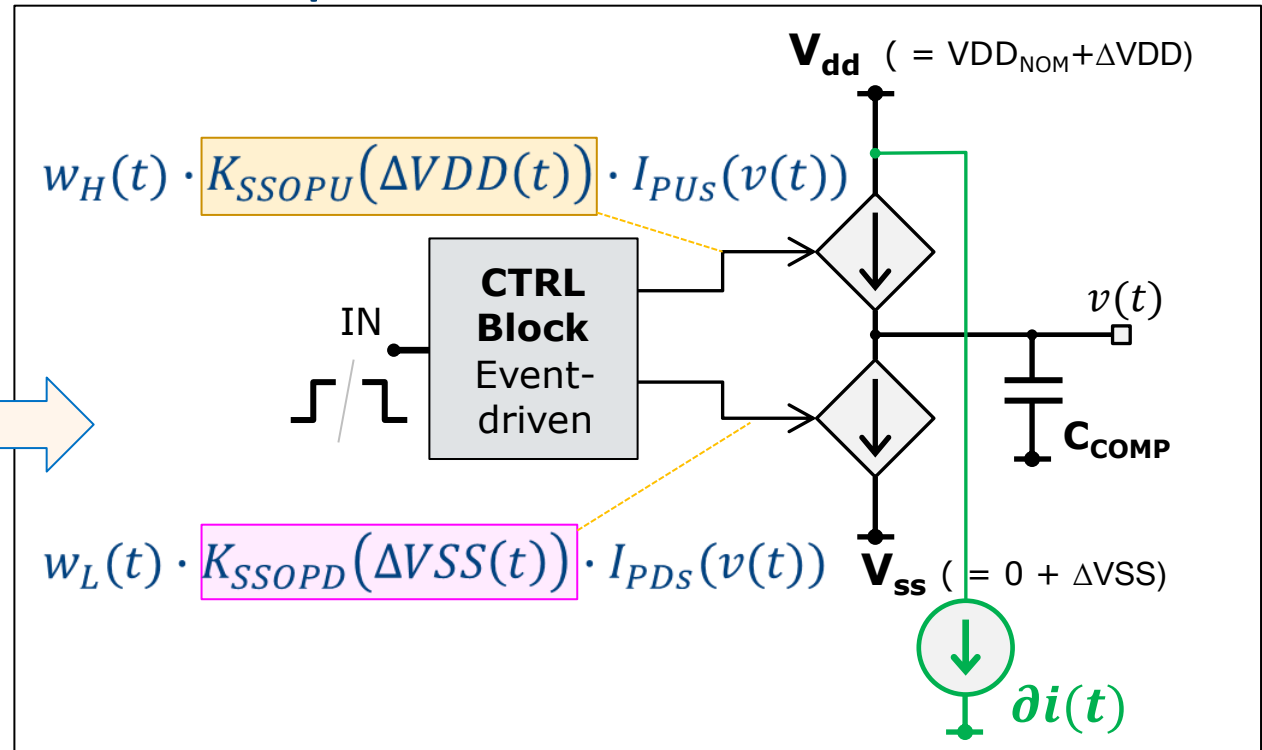
$$i(t) = w_H(t) \cdot K_{SSOPU}(\Delta v_{dd}) \cdot I_{PU}(v) + w_L(t) \cdot K_{SSOPD}(\Delta v_{ss}) \cdot I_{PD}(v) - C_{COMP} \frac{\partial v}{\partial t}$$

$$i_{dd}(t) = w_H(t) \cdot K_{SSOPU}(\Delta v_{dd}) \cdot I_{PU}(v) + \partial i(t)$$

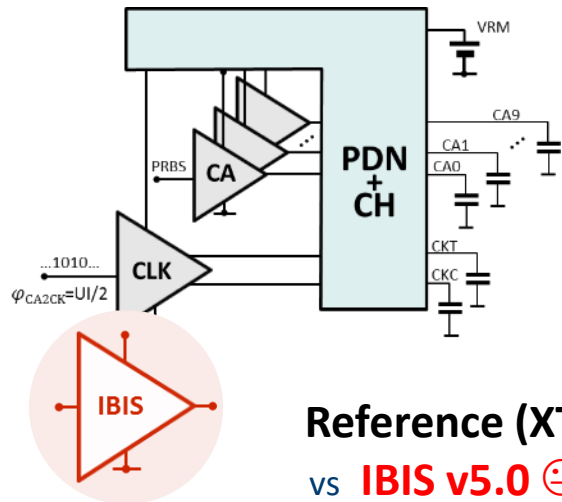
my_ibis_v5.ibs

```
[Model]
[Pull-Up]
[Pull-Down]
[ISSO PU]
[ISSO PD]
[C_comp]
[Rising Waveform]
[Composite Current]
[Falling Waveform]
[Composite Current]
```

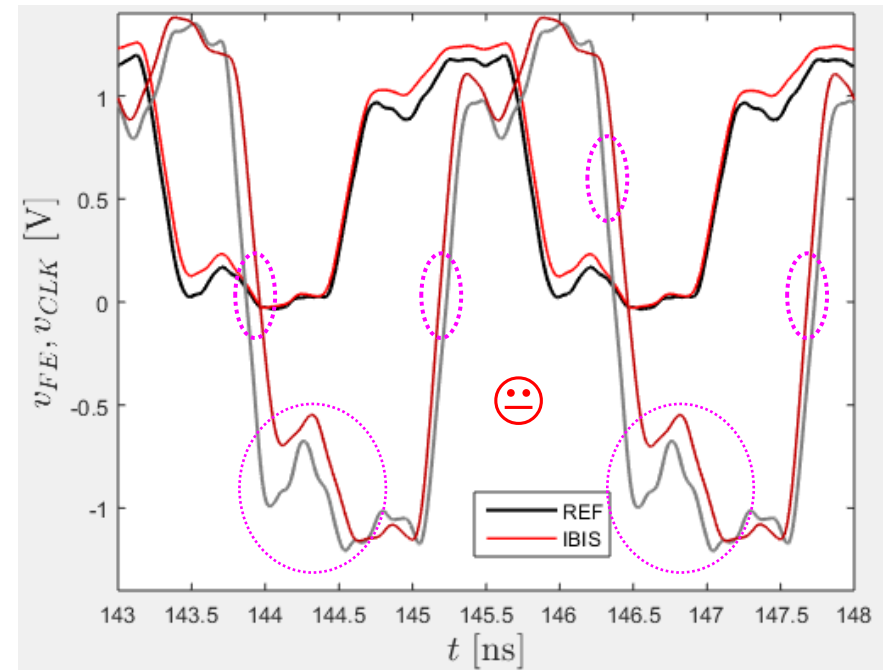
IBIS v5.0 Equivalent Electrical Circuit



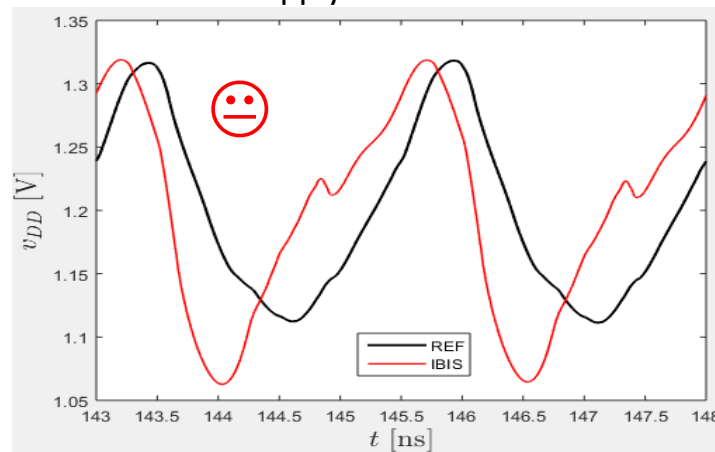
Validation



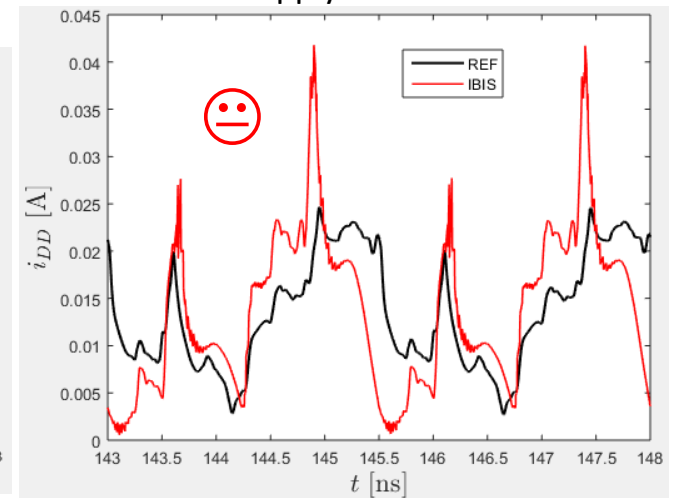
CLK/DATA Far-End Signals



Supply-Noise

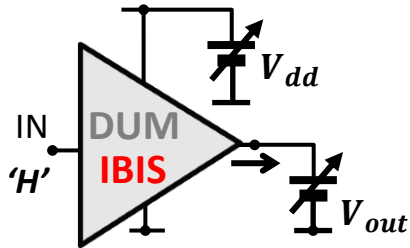


Supply-Current

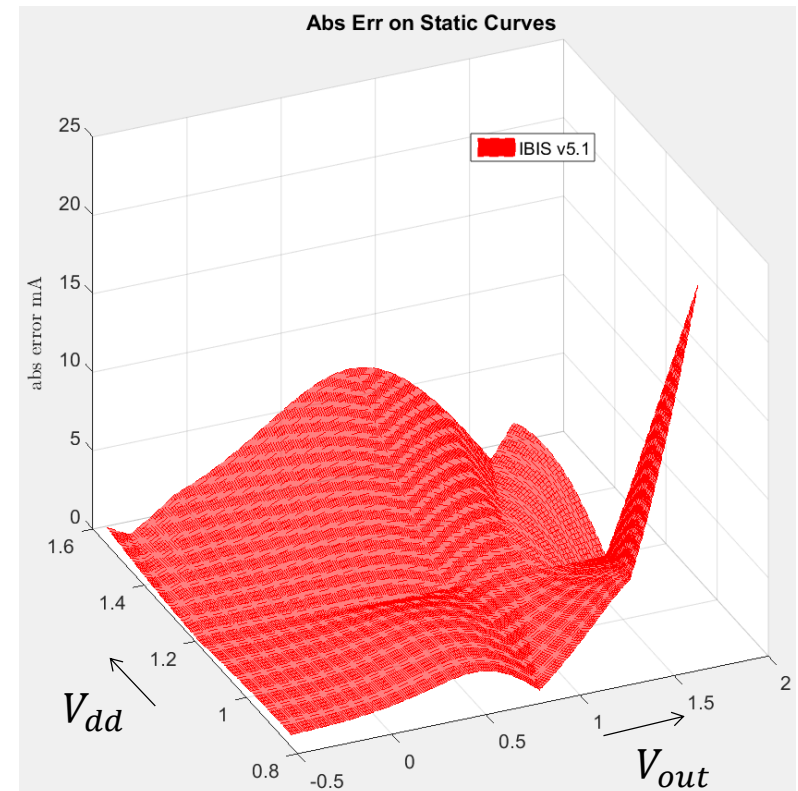
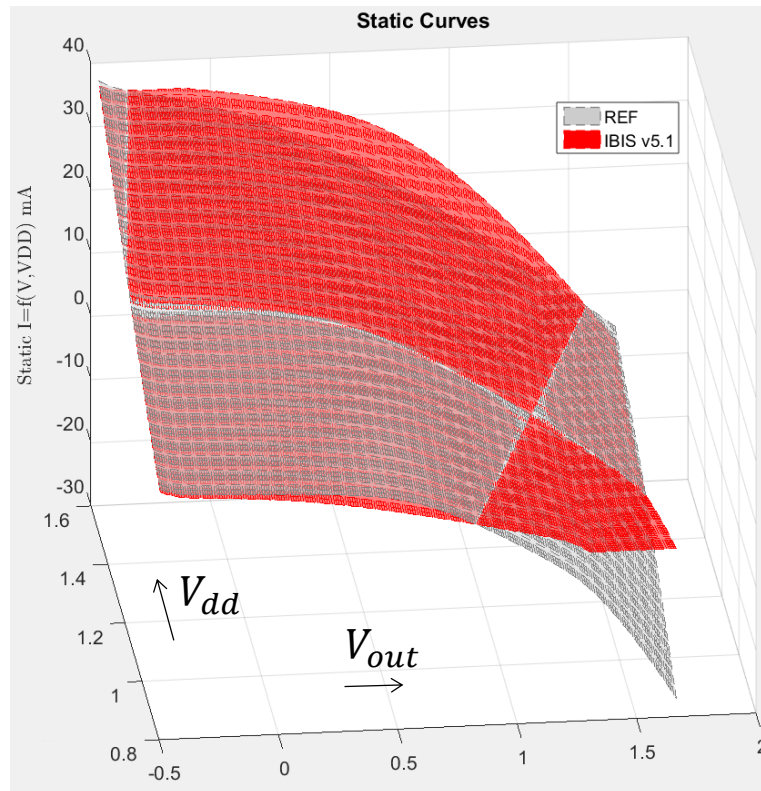


VDD $\Leftrightarrow$ Static Characteristics

*Nested .DC sweep
on Output and Supply ports*

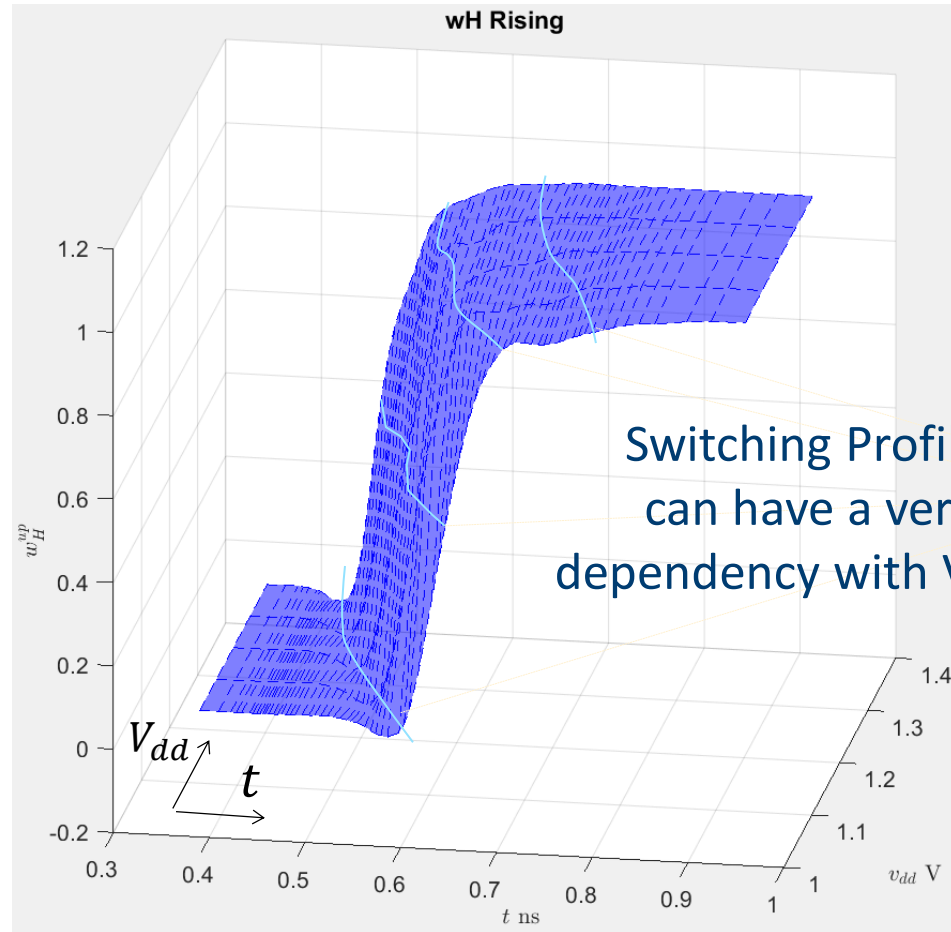
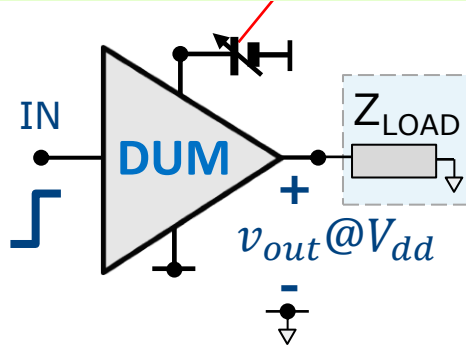


**Possible inaccuracy with
ISSO_PU(PD) approximation ?**



VDD $\Leftrightarrow$ Rising/Falling Waveforms

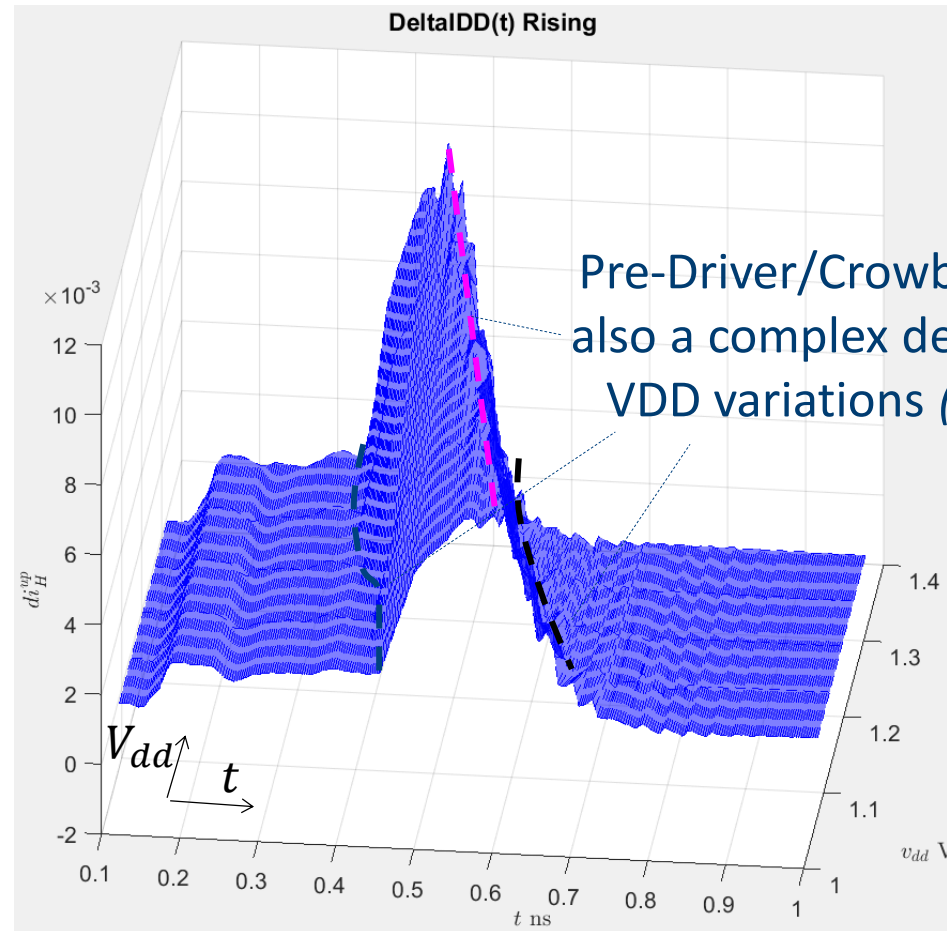
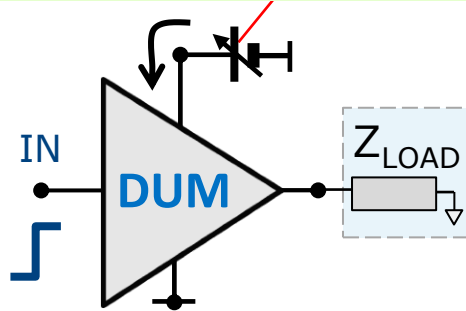
$$V_{dd} \in [80\%, \dots, 100\%, \dots, 120\%] \times V_{DD,NOM}$$



IBIS v5.0 model structure may be limited in representing this behavior

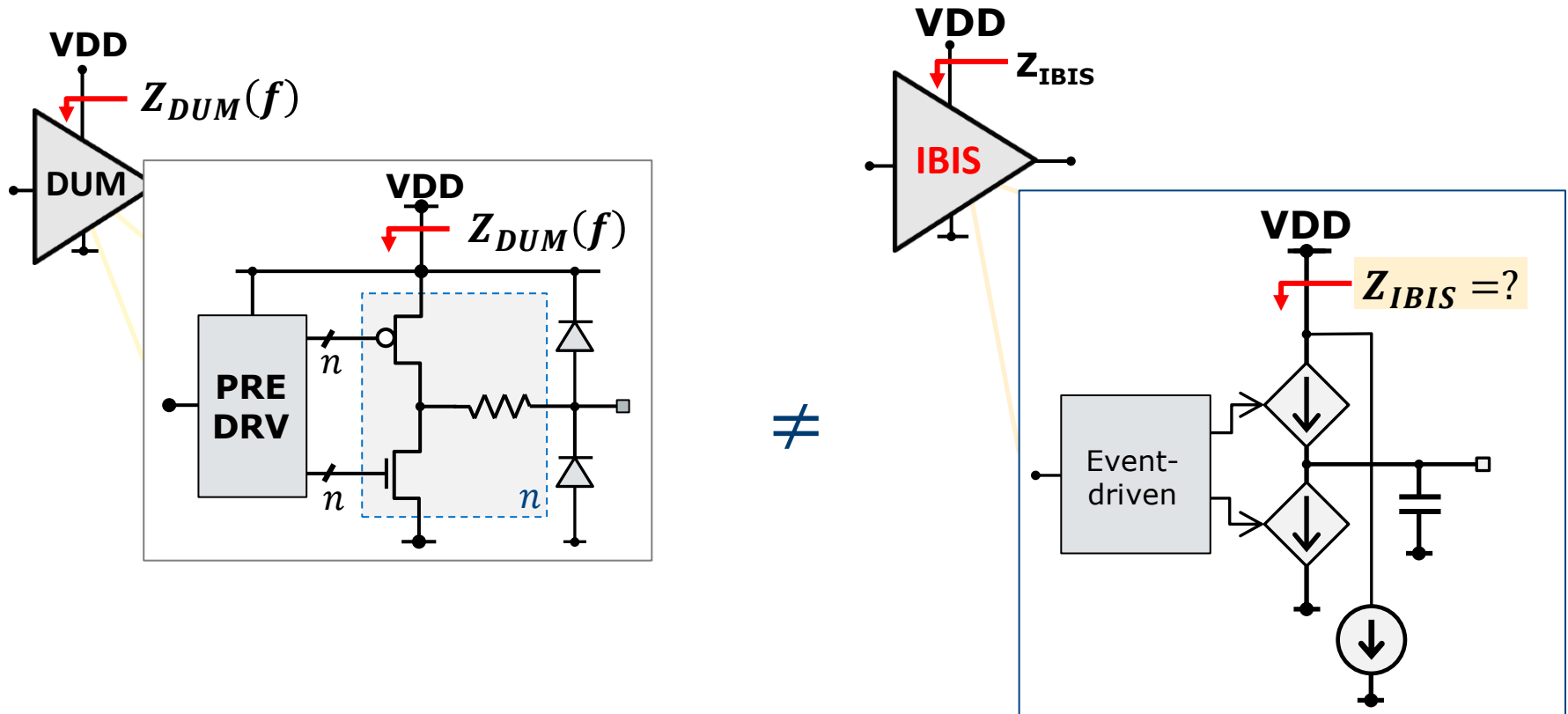
VDD $\Leftrightarrow$ Supply-Current [I_{COMP}]

$$V_{dd} \in [80\%, \dots, 100\%, \dots, 120\%] \times V_{DD,NOM}$$



IBIS v5.0 model structure may also be limited in representing this behavior

Dynamic Contribution to Supply-Current



How to correctly model
I/O-Buffer “supply-port impedance”?

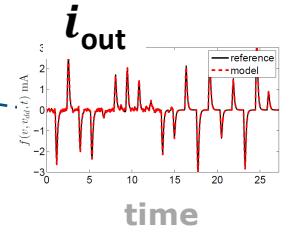
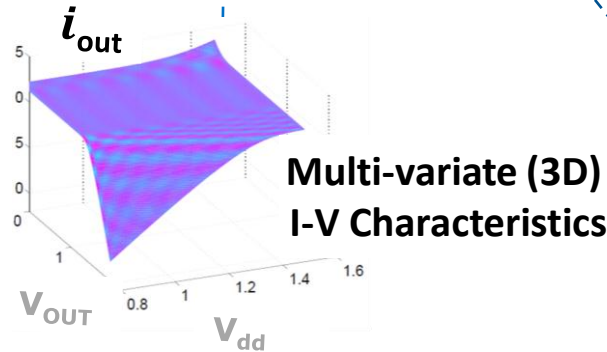
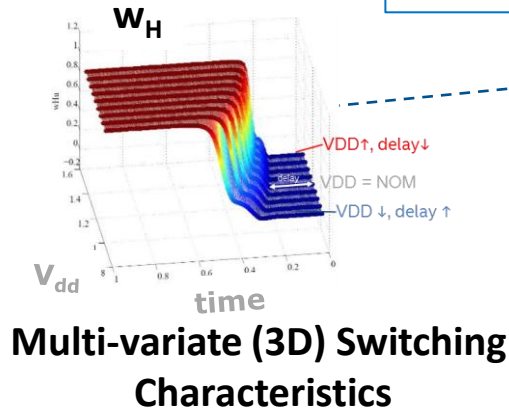
Enhanced I/O-Buffer Macromodels

Mpilog-class

Enhanced Two-Piece Models: R&D work

$$i(t) = w_H(t, v_{dd}) \cdot [I_{PU}(v, v_{dd}) + f_H(v, v_{dd})] + w_L(t, v_{dd}) \cdot [I_{PD}(v, v_{dd}) + f_L(v, v_{dd})]$$

$$i_{dd}(t) = w_H(t, v_{dd}) \cdot [I_{PU,S}(v, v_{dd}) + f_{H,S}(v, v_{dd})] + w_L(t, v_{dd}) \cdot [I_{PD,S}(v, v_{dd}) + f_{L,S}(v, v_{dd})] + \partial i(t, v_{dd})$$

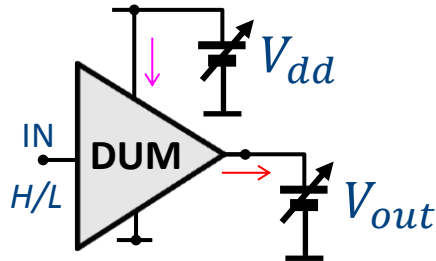


Multiple-Input Single-Output (MISO) Rational Functions (Time-Domain Vector-Fitting)

Explicit dependency with VDD in model sub-components

Mathematical structure $\Rightarrow$ **re-cast** as **Verilog-A** or **SPICE** circuit

Proposed Enhancements: Static Characteristics

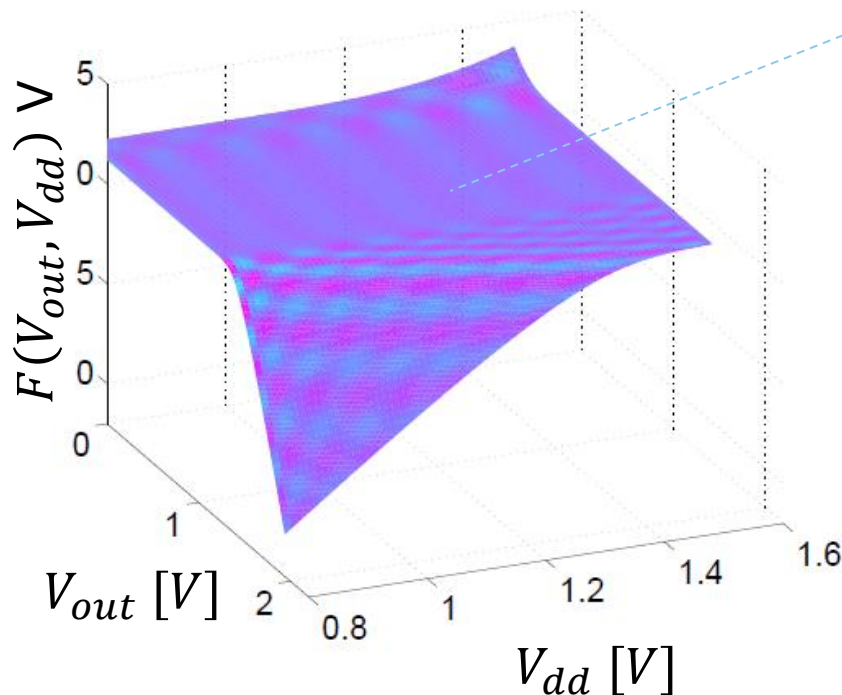


Static characterization
Testbench

The static characteristics are now extracted with **nested .DC sweeps** at **output and supply** ports.

(e.g., 1 output, 1 supply, 1 current: 3D-surface)

$$I_S = F(V_{out}, V_{dd})$$



Such 3D surfaces are calculated for:

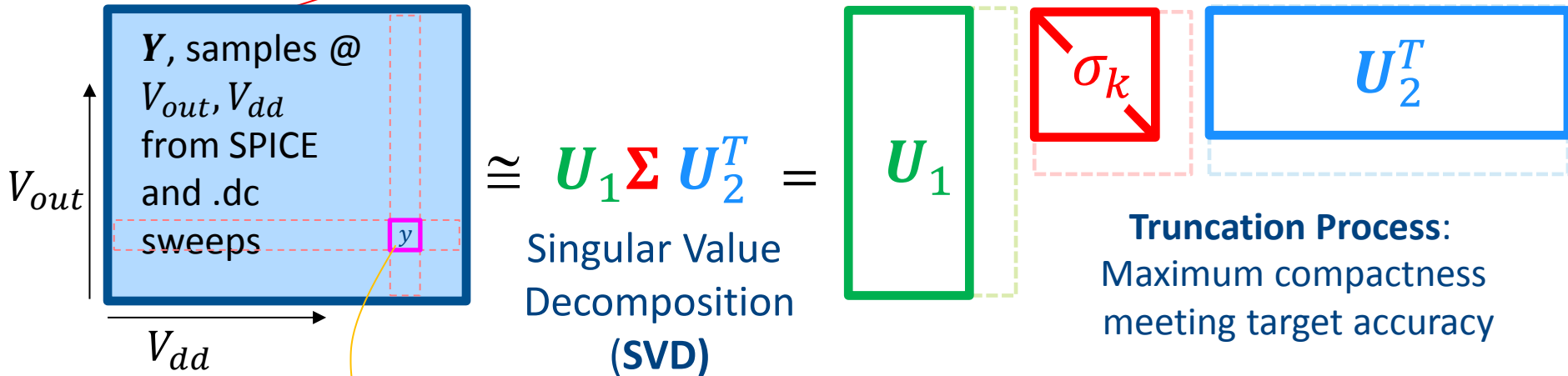
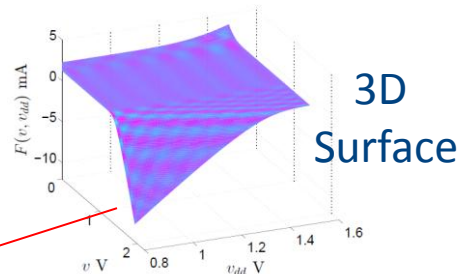
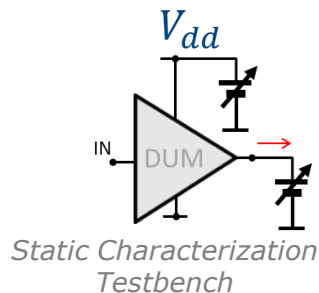
$$I_{SH}(V_{out}, V_{dd})$$

$$I_{SL}(V_{out}, V_{dd})$$

$$I_{dd,SH}(V_{out}, V_{dd})$$

$$I_{dd,SL}(V_{out}, V_{dd})$$

SVD Approximation of 3D Surfaces

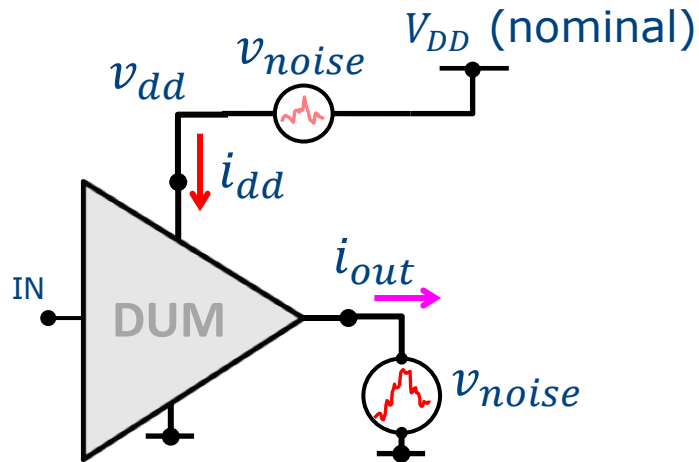


$$y \cong F(V_{out}, V_{dd}) = \sum_{k=1}^N \sigma_k \varphi_{1,k}(V_{out}) \varphi_{2,k}(V_{dd})$$

SVD-approximation $\Rightarrow$

- SPICE Netlist (VCVS, CCCS, ...)
- Verilog-A Code

Proposed Enhancements: Dynamic Characteristics

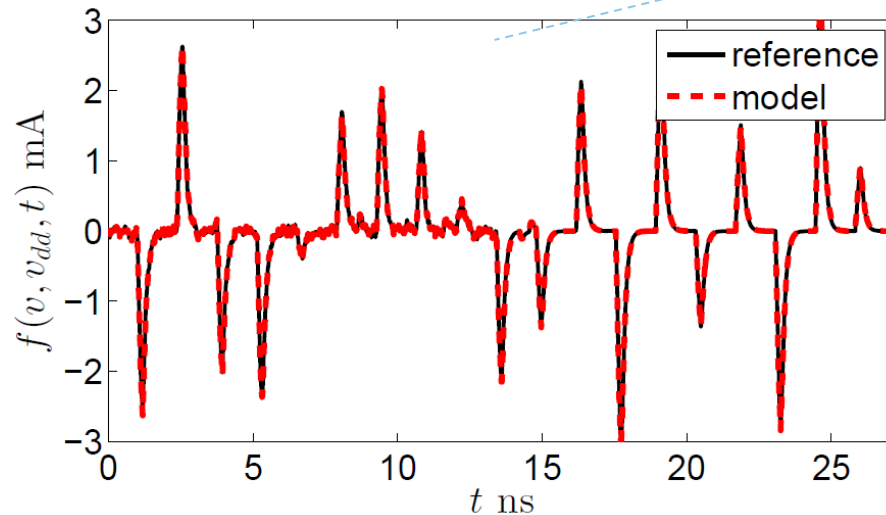


Dedicated $v_{out}(t)$ and $v_{dd}(t)$ stimuli are applied, simultaneously.

Dynamic characteristics = rational approximations using **Time-Domain Vector-Fitting (TD-VF)** algorithms.

$$i_{out,H} = f(v_{out}, v_{dd})$$

(e.g., pull-up dynamic MISO TDVF model)



Similar models are computed for:

$$i_{out,H}(v_{out}, v_{dd})$$

$$i_{out,L}(v_{out}, v_{dd})$$

$$i_{dd,H}(v_{out}, v_{dd})$$

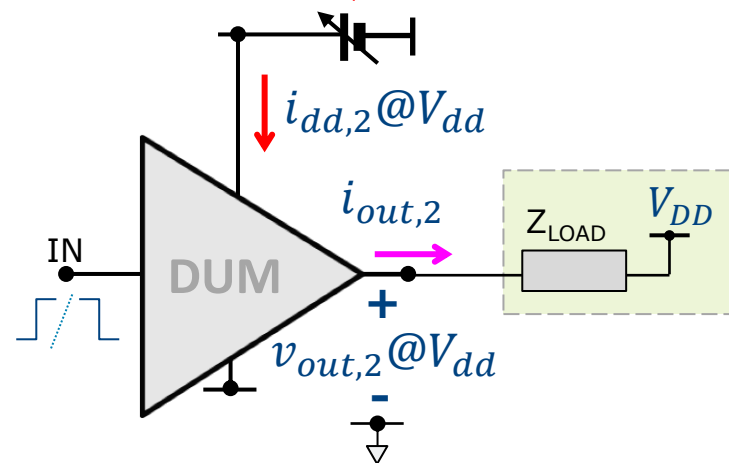
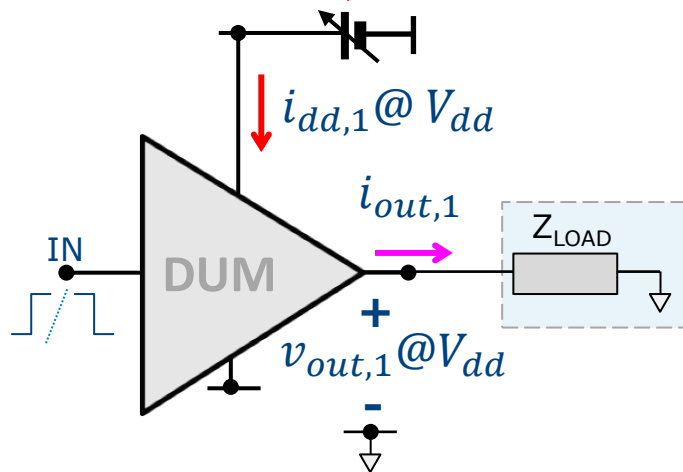
$$i_{dd,L}(v_{out}, v_{dd})$$

and implemented as:

- SPICE Netlist
- Verilog-A models

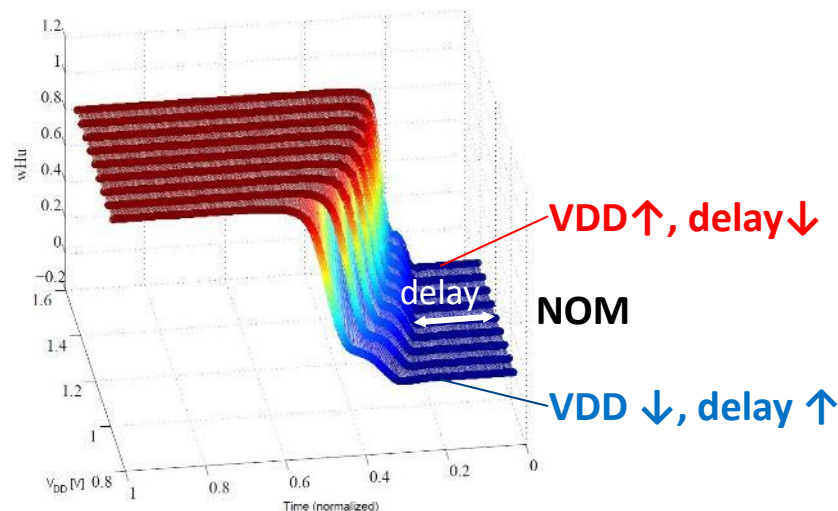
Proposed Enhancements: Weighting Functions

$$V_{dd} \in [80\%, \dots, 100\%, \dots, 120\%] \times V_{DD,NOM}$$



Weighting functions w_H and w_L are calculated for several V_{dd} values.

This allows the creation of 3D-surfaces $w_H(t, v_{dd})$ and $w_L(t, v_{dd})$ reproducing the complex dependency of the switching events with VDD.



Comparative Summary

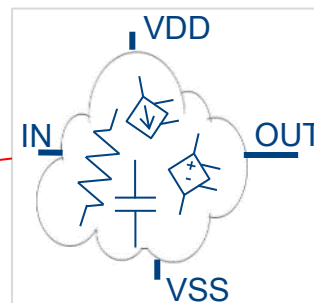
	IBIS v5.0	Enhanced Models
OUTPUT STATIC	2D I-V Tables	3D Surfaces $F_x(V_{out}, V_{dd})$
OUTPUT DYNAMIC	Capacitive C_{COMP}	State-space models $f_x(v_{out}, v_{dd})$
WEIGHTING FUNCTIONS	2EQ/2UK @VDD _{NOM} $k_U(t)$ and $k_D(t)$	3D Surfaces $w_{L2H}(t, v_{dd})$ and $w_{H2L}(t, v_{dd})$
SUPPLY CURRENT	$I_{COMP} - t$ Table	3D Surface $\delta_i(t, v_{dd})$
SUPPLY EFFECTS	Static Modulation $K_{SSO_PU(PD)}$	3D surfaces & MISO models Static/Dyn/Timing Effects

MPILOG Model Implementation

Mpilog models can be synthesized as:

- **SPICE Netlists**
- **Verilog-A Modules**
- IBIS (v5.1/6.0) 😊
- **IBIS using [External Model]**

mpilog.cir



mpilog.va

```
// Output + supply ports driver macromodel
// VERILOG-A implementation autogenerated by Mpilog

`include "constants.vams"
`include "disciplines.vams"
// *****
// COMPLETE MACROMODEL
// *****
module mpilog_model (v_in,v_io,vdd_io,ref_io,v_oe);

// ELECTRICAL VARIABLES
electrical v_in,v_io,vdd_io,ref_io,v_oe;
electrical w1,w2,f1,f2,fs1,fs2,f7,fs7;
electrical f3,f4,fs3,fs4,di,f8,fs8;
electrical u1,u2;

// PARAMETERS
parameter real PVDDcore=1; // logic core nominal voltage
parameter real PVDD=1.2; //output power-supply nominal voltage

analog begin
// MODEL STRUCTURE...
```

```
[External Model]
Language Verilog-A(MS)

| Corner corner_name file_name circuit_name (module)
Corner Typ mpilog.va mpilog_model
Corner Min NA NA
Corner Max NA NA

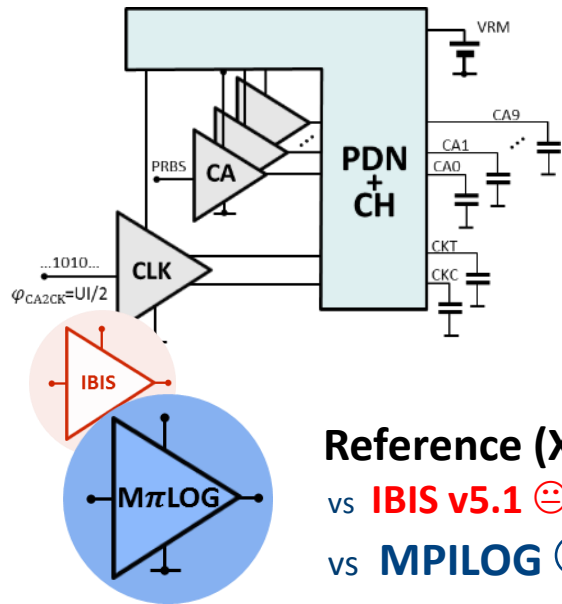
| Ports List of port names (in same order as in Verilog-A(MS))
| v_in v_out vdd_io ref_io v_oe
Ports my_drive A_signal_pos A_puref A_pdref my_enable

| D_to_A d_port port1 port2 vlow vhigh trise tfall corner_name
D_to_A D_drive my_drive A_pdref 0.0 1.1 0.1n 0.1n Typ
D_to_A D_enable my_enable A_pdref 0.0 1.1 0.1n 0.1n Typ

[End External Model]
```

mpilog.ibs

Validations

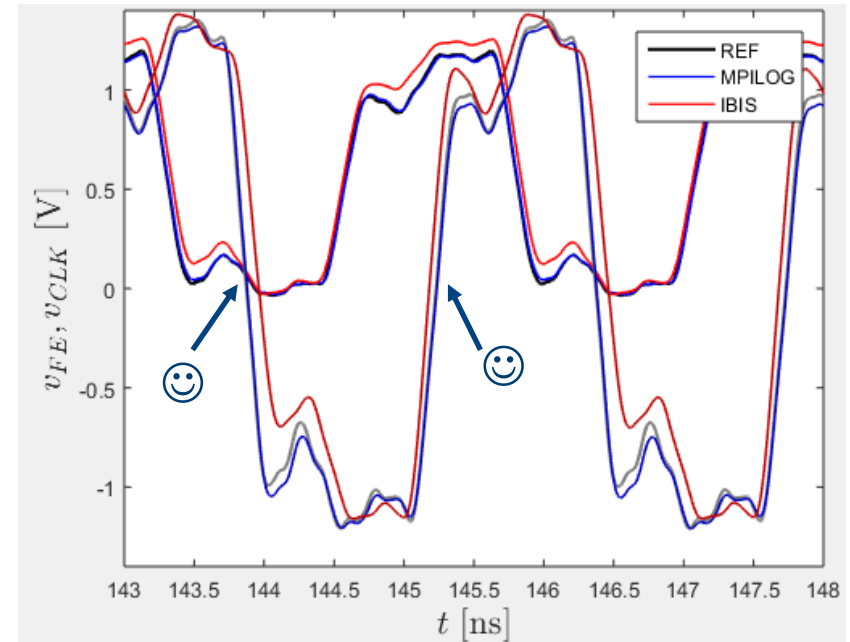


Reference (XTOR-level)

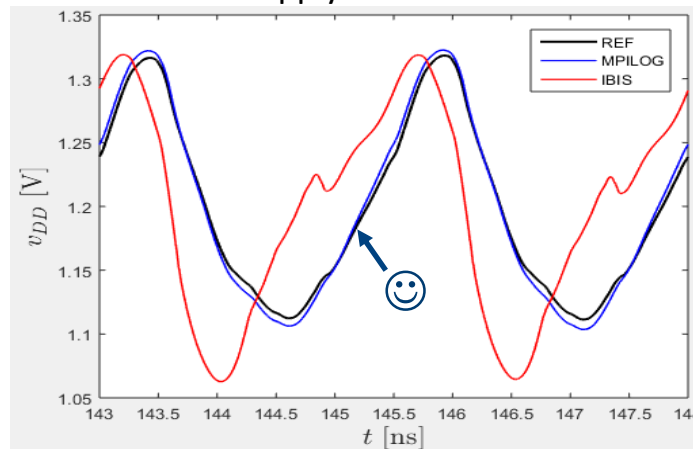
vs **IBIS v5.1** ☹️

vs **MPILOG** 😊

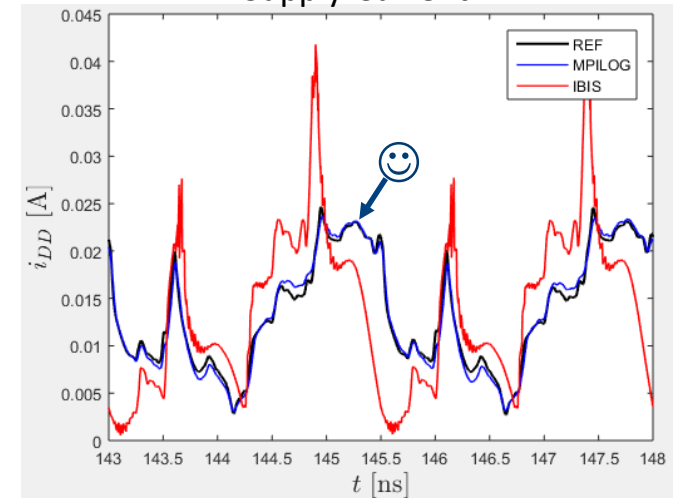
CLK/DATA Far-End Signals



Supply-Noise

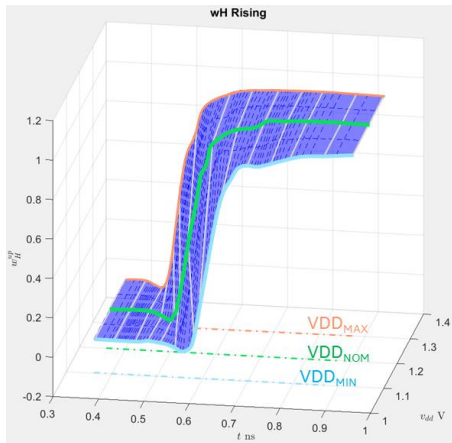


Supply-Current



Possible Enhancements to IBIS models?

3-curve approx. of 3D-Surfaces in IBIS



How to include 3-curve
approx. data in an IBIS file?

[Model] DDR_PAD			
<i>variable</i>	<i>typ</i>	<i>min</i>	<i>max</i>
[Temperature Range]	25	-30	125
[Voltage Range]	1.2	1.1	1.3
[Rising Waveform]			
<i>Time</i>	<i>v(typ)</i>	<i>v(min)</i>	<i>v(max)</i>
0			
25ps			
...			
1.21ns			
1.22ns			

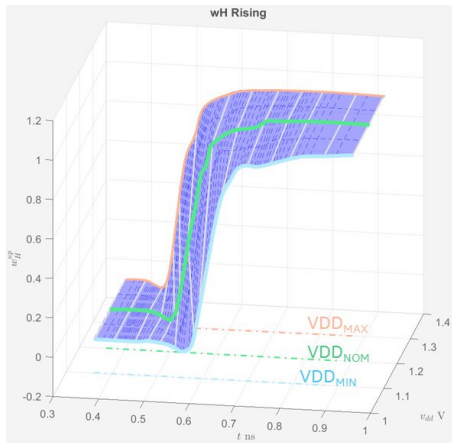
IBIS v5.1:

Process: TT	Process: SS	Process: FF
VDD: TYP	VDD: MIN	VDD: MAX
Temp: Typ	Temp: Max	Temp: Min

For all IBIS table ...
PU/PD
Rising/Falling V-t
Rising/Falling I-t

**1 [Model],
3 PVT Corners**

3-curve approx. of 3D-Surfaces in IBIS



How to include 3-curve
approx. data in an IBIS file?

[Model] DDR_PAD			
variable	typ	min	max
[Temperature Range]	25	-30	125
[Voltage Range]	1.2	1.1	1.3
[Rising Waveform]			
Time	v(typ)	v(min)	v(max)
0			
25ps			
...			
1.21ns			
1.22ns			

For all IBIS table ...
PU/PD
Rising/Falling V-t
Rising/Falling I-t

~~IBIS v5.1:~~

Process: TT Process: SS Process: FF
VDD: TYP VDD: MIN VDD: MAX
Temp: Typ Temp: Max Temp: Min

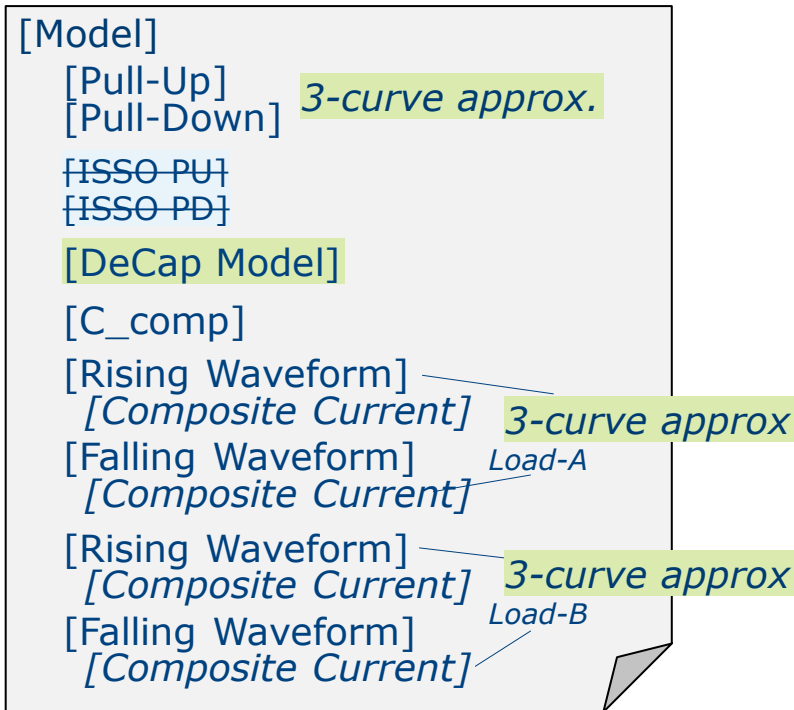
~~1 [Model],
3 PVT Corners~~

**“enhanced”
IBIS**

Process: TT Process: TT Process: TT
VDD: TYP VDD: MIN VDD: MAX
Temp: 25 Temp: 25 Temp: 25

**1 [Model],
1 PT Corner** (e.g., TT/25C)
Accuracy @SI&PI
(capture VDD-effects)

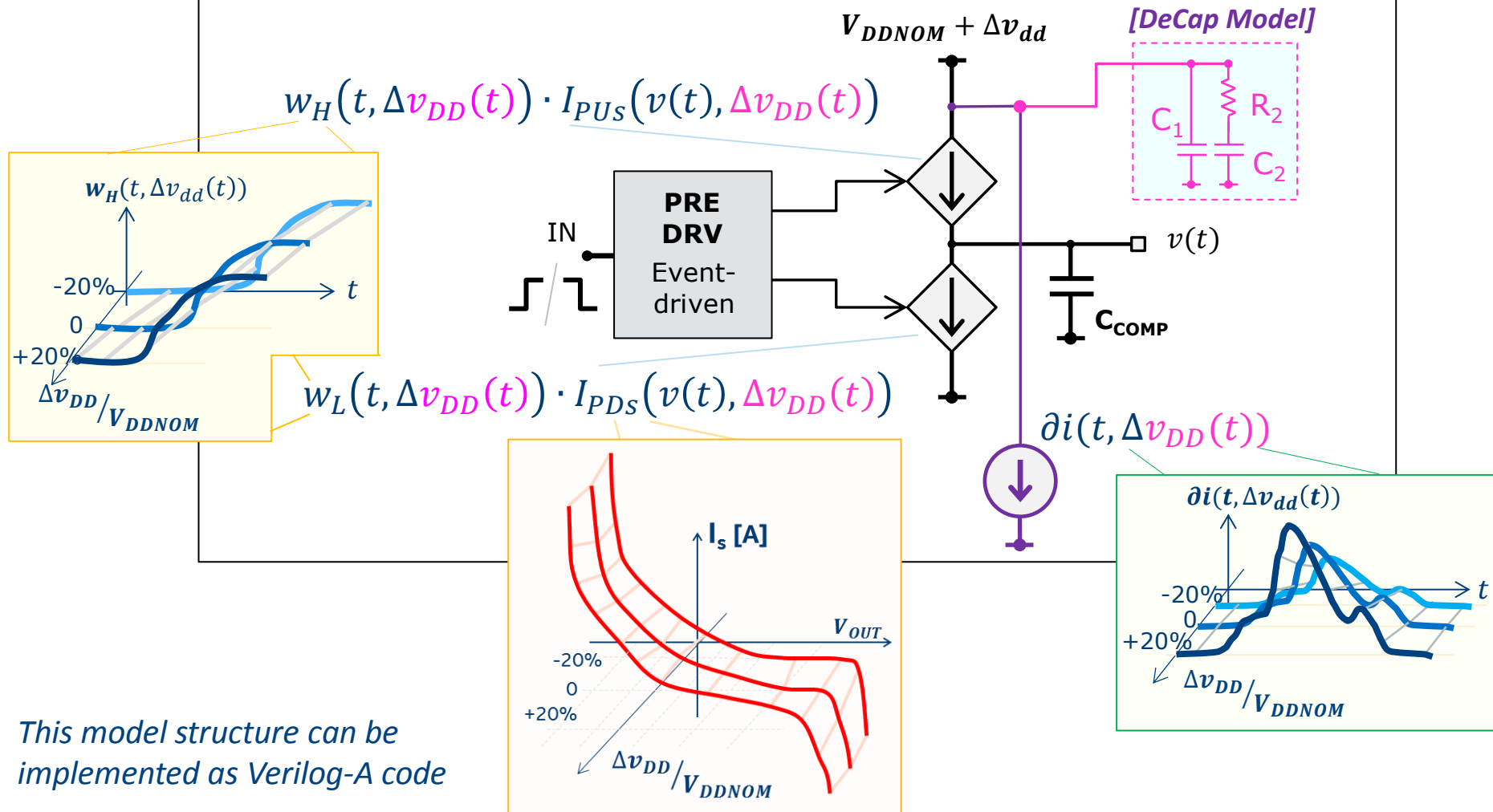
(Proposed) “Enhancements” to IBIS Models



- Removal of [ISSO PU] and [ISSO PD]
- **3-curve approximations**
 - ✓ 3D PU/PD Characteristic
 - ✓ 3D Rising/Falling V-t Tables
 - ✓ 3D Rising/Falling [Composite Current]
- **[DeCap Model]**
 - ✓ $C1 \parallel (R2+C2)$ for “supply impedance”

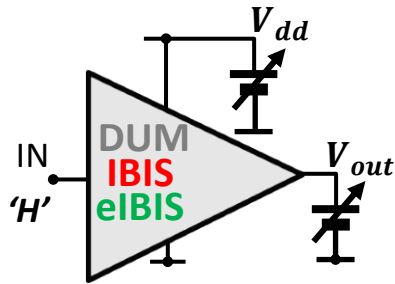
(Proposed) “Enhanced” IBIS Models

Proposed Enhanced IBIS Equivalent Electrical Circuit



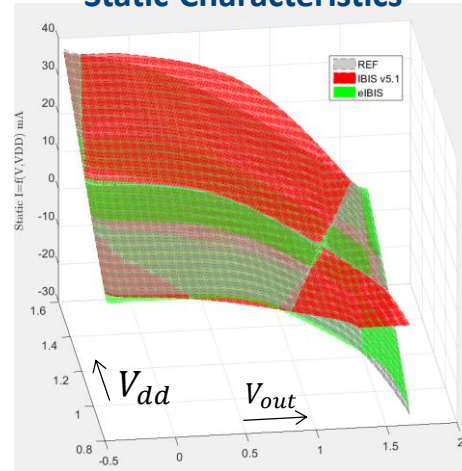
This model structure can be implemented as Verilog-A code

Multi-variate Surfaces

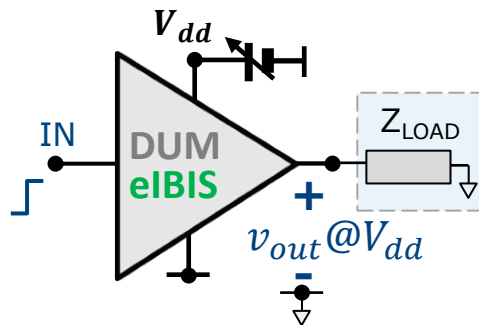
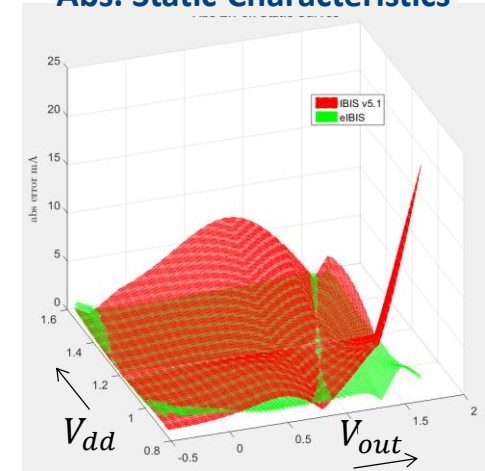


*Nested .DC sweep
on Output and Supply ports*

Static Characteristics

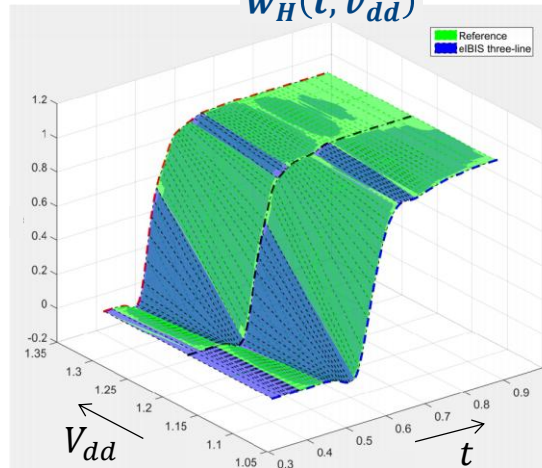


Abs. Static Characteristics

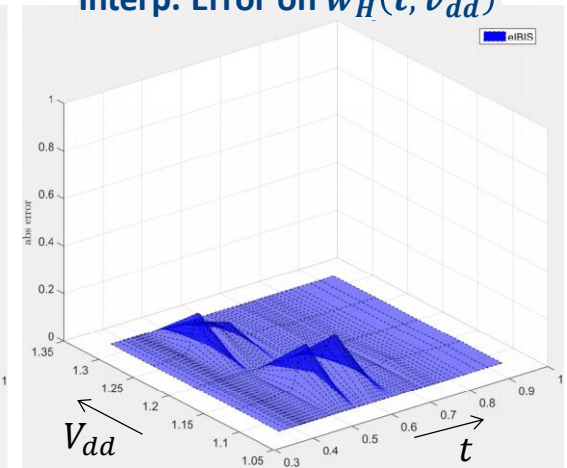


*.TRAN Rising Waveforms applying
different VDD values*

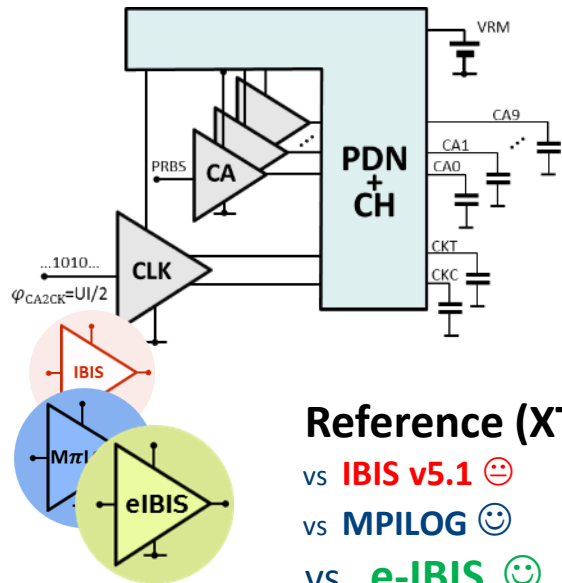
$w_H(t, v_{dd})$



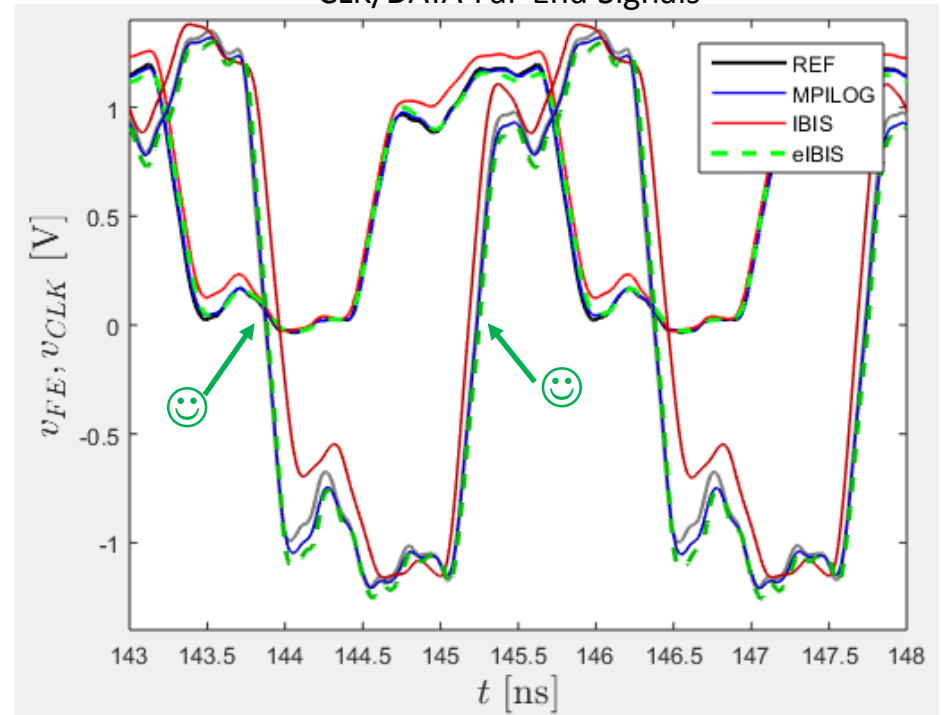
Interp. Error on $w_H(t, v_{dd})$



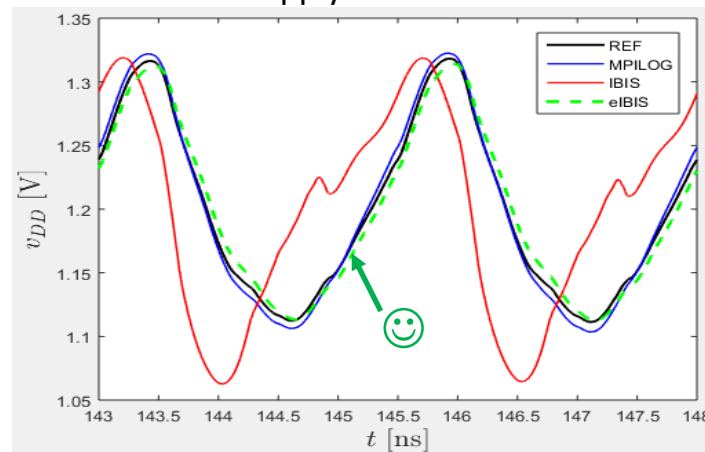
Validation



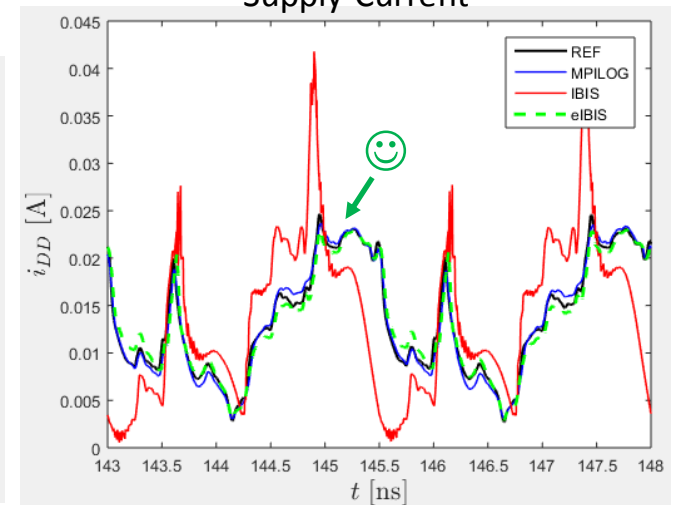
CLK/DATA Far-End Signals



Supply-Noise



Supply-Current



Conclusions

Enhanced two-piece model structure to accurately reproduce currents and voltages at **output** and **supply ports** :

- ✓ **SVD + truncation-process** for (multi-dimensional) Static Char.
- ✓ Multiple-Input **TDVF** for Dynamic Characteristics
- ✓ 3D switching characteristics $w(t, v_{dd})$

Flexible and **modular** approach using **Mpilog**
Implementations possible in **SPICE/Verilog-A**

Identification of **potential limitations** of IBIS models power-awareness
Set of **possible enhancements** to IBIS
(*3-curve approx. & VDD-effects, impedance at supply-port, ...*)

Validation tests highlight **excellent accuracy** in **SI/PI co-simulations**

Thank you for the attention!